# EE 330 Lecture 32

## Cascaded Amplifiers Analysis and Design

#### **Basic Amplifier Gain Table**



Can use these equations only when small signal circuit is EXACTLY like that shown !!

## **Basic Amplifier Characteristics Summary**



## Cascaded Amplifier Analysis and Operation



• Systematic Methods of Analysis/Design will be Developed

#### One or more couplings of nonadjacent stages



Less Common

Analysis Generally Much More Involved, Use Basic Circuit Analysis Methods

## Cascaded Amplifier Analysis and Operation

Adjacent Stage Coupling Only



Systematic Methods of Analysis/Design will be Developed

Case 1: All stages Unilateral

Case 2: One or more stages are not unilateral

#### **Repeat from earlier discussions on amplifiers**

## **Cascaded Amplifier Analysis and Operation**

Case 1: All stages Unilateral



Accounts for all loading between stages !

## Cascaded Amplifier Analysis and Operation

Case 2: One or more stages are not unilateral

#### Standard two-port cascade



Analysis by creating new two-port of entire amplifier quite tedious because of the reverse-gain elements

#### Right-to-left nested R<sub>inx</sub>, A<sub>VKX</sub> approach





Determine the voltage gain of the following circuit in terms of the smallsignal parameters of the transistors. Assume  $Q_1$  and  $Q_2$  are operating in the Forward Active region and  $C_1...C_4$  are large.



In this form, does not look "EXACTLY" like any of the basic amplifiers !





Will calculate A<sub>V</sub> by determining the three ratios (not voltage gains of dependent source):

$$\mathsf{A}_{\mathsf{V}} = \frac{v_{\mathsf{out}}}{v_{\mathsf{in}}} = \frac{v_{\mathsf{out}}}{v_{\mathsf{B}}} \frac{v_{\mathsf{B}}}{v_{\mathsf{A}}} \frac{v_{\mathsf{A}}}{v_{\mathsf{in}}} = \mathsf{A}_{\mathsf{V2}} \mathsf{A}_{\mathsf{V1}} \mathsf{A}_{\mathsf{V0}}$$



$$\mathsf{A}_{\mathrm{V2}} = \frac{\boldsymbol{v}_{\mathrm{out}}}{\boldsymbol{v}_{\mathrm{B}}} \cong -\frac{\mathsf{R}_{\mathrm{6}}//\mathsf{R}_{\mathrm{8}}}{\mathsf{R}_{\mathrm{7}}}$$

 $R_{in2}\cong\beta R_7$ 





 $\mathbf{R}_{\text{in2}}$ 

$$R_{in2} \cong \beta R_7$$



$$A_{V2} = \frac{v_{out}}{v_{B}} \cong -\frac{R_{6}//R_{8}}{R_{7}}$$
$$R_{in2} \cong \beta R_{7}$$





 $R_{in1} \cong r_{\pi 1}$ 







$$A_{V0} = \frac{v_A}{v_{in}} \cong \frac{R_1 / / R_2 / / R_{in1}}{R_S + R_1 / / R_2 / / R_{in1}}$$



Thus we have

### Formalization of cascade circuit analysis working from load to input: (when stages are unilateral or not unilateral)



R<sub>ink</sub> includes effects of all loading Must recalculate if any change in loading Analysis systematic and rather simple

$$\frac{\boldsymbol{v}_{\text{OUT}}}{\boldsymbol{v}_{\text{IN}}} = \frac{\boldsymbol{v}_{1}}{\boldsymbol{v}_{1}} \frac{\boldsymbol{v}_{2}}{\boldsymbol{v}_{1}} \frac{\boldsymbol{v}_{3}}{\boldsymbol{v}_{2}} \frac{\boldsymbol{v}_{\text{OUT}}}{\boldsymbol{v}_{3}}$$

This was the approach used in analyzing the previous cascaded amplifier



Observation: By working from the output back to the input we were able to create a sequence of steps where the circuit at each step looked EXACTLY like one of the four basic amplifiers. Engineers often follow a design approach that uses a cascade of the basic amplifiers and that is why it is often possible to follow this approach to analysis.

Two other methods could have been used to analyze this circuit

What are they?



Two other methods could have been used to analyze this circuit

#### 1. Create a two-port model of the two stages

(for this example, since the first-stage is unilateral, it can be shown that )

$$A_{V} = \frac{v_{out}}{v_{in}} = \frac{v_{A}}{v_{in}} \frac{v_{B}}{v_{A}} \frac{v_{out}}{v_{B}}$$



Two other methods could have been used to analyze this circuit

2. Put in small-signal model for Q<sub>1</sub> and Q<sub>2</sub> and solve resultant circuit

(not too difficult for this specific example but time consuming )



#### Express in terms of small-signal parameters







$$A_{v} = \frac{v_{out}}{v_{2}} \frac{v_{2}}{v_{1}} \frac{v_{1}}{v_{in}} \cong \left[-g_{m4} \left(R_{D} / R_{L}\right)\right] \left[1\right] \left[\frac{-g_{m1}}{g_{m2} + \left(\beta_{3} \left(R_{B1} / R_{B2}\right)\right)^{-1}}\right]$$

# High-gain BJT amplifier



$$\mathsf{A}_{\mathsf{V}} = \frac{-\mathsf{g}_{\mathsf{m}}}{\mathsf{g}_{\mathsf{0}} + \mathsf{G}_{\mathsf{C}}} \cong -\mathsf{g}_{\mathsf{m}}\mathsf{R}_{\mathsf{C}}$$

To make the gain large, it appears that all one needs to do is make  $R_c$  large !

$$A_V \cong -g_m R_C = \frac{-I_{CQ} R_C}{V_t}$$

But V<sub>t</sub> is fixed at approx 25mV and for good signal swing,  $I_{CQ}R_C < (V_{DD}V_{EE})/2$ 

$$|A_V| < \frac{V_{DD} - V_{EE}}{2V_t}$$
  
$$|A_V| < \frac{5V}{2 \cdot 25mV} = 100$$

- Gain is practically limited with this supply voltage to around 100
- And in extreme case, limited to 200 with this supply voltage with very small signal swing

# High-gain MOS amplifier

$$A_{V} = \frac{-g_{m}}{g_{0} + G_{D}} \cong -g_{m}R_{D}$$



To make the gain large, it appears that all one needs to do is make  $R_D$  large !

$$A_{V} \cong -g_{m}R_{D} = \frac{-2I_{DQ}R_{D}}{V_{EB}}$$

But V<sub>EB</sub> is practically limited to around 100mV and for good signal swing,  $I_{DQ}R_D < (V_{DD}V_{SS})/2$ 

$$\left|\mathsf{A}_{\mathsf{V}}\right| < rac{\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{SS}}}{\mathsf{V}_{\mathsf{EB}}}$$

If  $V_{DD}$  -  $V_{SS}$  = 5V and  $V_{EB}$  = 100mV,

$$|A_V| < \frac{5V}{100mV} = 50$$

Gain is practically limited with this supply voltage to around 50

Are these fundamental limits on the gain of the BJT and MOS Amplifiers?



# High-gain amplifier



This gain is very large !

Too good to be true !

Need better model of MOS device!



# High-gain amplifier



And no dooign peremeters offect the ge

And no design parameters affect the gain

But how can we make a current source?

# High-gain amplifier



Same gain with both npn and pnp transistors

How can we build the ideal current source?

What is the small-signal model of an actual current source?

# End of Lecture 32